

IN THE CLAIMS:

1-9. (Canceled)

10. (Currently Amended) A thin film transistor comprising a semiconductor film, a first gate insulating film, a second gate insulating film and a gate electrode sequentially formed on one major surface of a substrate in that order,

wherein said first gate insulating film covers said semiconductor film,

said second gate insulating film is made of a material for supplying hydrogen to said semiconductor film,

said second gate insulating film is integrally formed over said first gate insulating film, which covers said the semiconductor film, and

said second gate insulating film has a smaller film thickness in a region not covered with said gate electrode than that in a region covered with said gate electrode, and

said second gate insulating film covers said first gate insulating film in said region not covered with said gate electrode in which said second gate insulating film has said smaller film thickness.

11. (Original) The thin film transistor according to claim 10, wherein said first gate insulating film is a silicon oxide film and said second gate insulating film is a silicon nitride film.

12. (Original) The thin film transistor according to claim 10, wherein said semiconductor film is a poly-silicon film.

13. (Currently Amended) A thin film transistor comprising a semiconductor film, a first gate insulating film, a second gate insulating film and a gate electrode sequentially formed on one major surface of a substrate in that order, and an interlayer insulating film having a thickness larger than that of said second gate insulating film in a region covered with said gate electrode, said interlayer insulating film covering said gate electrode and covering said second gate insulating film

in a region where said gate electrode is not formed, and

wherein said first gate insulating film covers said semiconductor film,

said second gate insulating film is made of a material for supplying hydrogen to said semiconductor film,

said second gate insulating film is integrally formed over said first gate insulating film, which covers said the semiconductor film; and

said second gate insulating film has a smaller film thickness in a region not covered with said gate electrode than that in said region covered with said gate electrode; and

said second gate insulating film covers said first gate insulating film in said region not covered with said gate electrode in which said second gate insulating film has said smaller film thickness.

14. (Previously Presented) The thin film transistor according to claim 13, wherein said first gate insulating film is a silicon oxide film and said second gate insulating film is a silicon nitride film.

15. (Previously Presented) The thin film transistor according to claim 13, wherein said semiconductor film is a poly-silicon film.

16. (New) The thin film transistor according to claim 10, wherein said second insulating film has a smaller film thickness from an end position of said gate electrode covering said second insulating film.

17. (New) The thin film transistor according to claim 13, wherein said second insulating film has a smaller film thickness from an end position of said gate electrode covering said second insulating film.